Listing of the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a substrate;

an electrode, the electrode being formed on the substrate;

a through-hole being formed through the electrode and the substrate in a stacking direction of the electrode and the substrate, the through-hole having a first diameter in the substrate that is smaller than a second diameter in the electrode;

a conductive member being inserted into the through-hole;

an insulating material, being disposed between the electrode and the conductive member, the insulating material including a wall portion located higher than at least the electrode; and

at least an interlayer dielectric being formed between the substrate and the electrode, the through-hole being formed in the interlayer dielectric, and surfaces of the interlayer dielectric and substrate in the through-hole being formed to have a level difference in a boundary area between the substrate and the interlayer dielectric,

the conductive member being formed over the wall portion of the insulating material from the through-hole and being connected with the electrode.

2. (Original) The semiconductor device as defined in claim 1,

wherein the insulating material is formed to cover an upper surface of the electrode and a surface in the through-hole, and includes a connection hole for connecting at least the electrode with the conductive member at a position differing from the through-hole, the wall portion being disposed between the connection hole and the through-hole.

3-4. (Canceled)

5. (Original) The semiconductor device as defined in claim 1,

wherein the conductive member functions as a connection terminal which secures electrical connection in an axial direction of the through-hole.

6. (Original) The semiconductor device as defined in claim 1,

wherein a part of the conductive member projects outward from the through-hole on a side of the substrate opposite to a side on which the electrode is formed.

7. (Original) A semiconductor device comprising a plurality of the semiconductor devices as defined in claim 1 which are stacked, each of the semiconductor devices being electrically connected through the conductive members.

8. (Original) A circuit board comprising the semiconductor device as defined in claim 1.

9. (Original) An electronic instrument comprising the circuit board as defined in claim 8.

10-15. (Canceled)